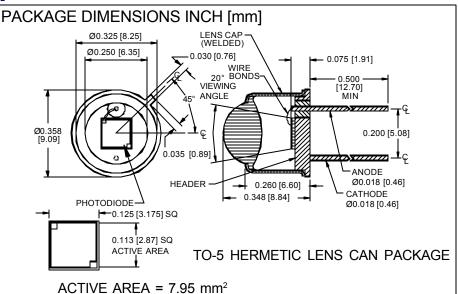
# PHOTONIC Silicon Photodiode, Blue Enhanced Photoconductive DETECTORS INC. (OP913SL Industry Equivalent) Lens Type PDB-C119-LC





**RESPONSIVITY (AW)** 

#### FEATURES

- Narrow angle
- High speed
- · Large active area
- · Low capacitance

## DESCRIPTION

The **PDB-C119-LC** is a silicon, PIN planar diffused, blue enhanced photodiode. Ideal for high speed photoconductive applications. Packaged in a hermetic TO-5 metal can with a glass lens window cap.

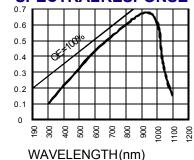
#### **APPLICATIONS**

- Bar code detector
- Encoder sensor
- Laser detection
- Instrumentation

### **ABSOLUTE MAXIMUM RATING** (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
Vbr	Reverse Voltage		100	V
T <sub>STG</sub>	Storage Temperature	-55	+150	°C
To	Operating Temperature Range	-40	+125	°C
Ts	Soldering Temperature*		+240	°C
Ι	Light Current		500	mA

#### SPECTRALRESPONSE



\*1/16 inch from case for 3 secs max

#### ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
lsc	Short Circuit Current	H = 100 fc, 2850 K	90	110		$\mu$ A
ΙD	Dark Current	H = 0, V <sub>R</sub> = 10 V		5	20	nA
Rsh	Shunt Resistance	H = 0, V <sub>R</sub> = 10 mV	150	300		MΩ
TC RSH	RSH Temp. Coefficient	H = 0, V <sub>R</sub> = 10 mV		-8		% / °C
CJ	Junction Capacitance	H = 0, V <sub>R</sub> = 10 V**		15	20	pF
λrange	Spectral Application Range	Spot Scan	350		1100	nm
λρ	Spectral Response - Peak	Spot Scan		950		nm
Vbr	Breakdown Voltage	I = 10 μA	75	100		V
NEP	Noise Equivalent Power	V <sub>R</sub> = 10 V @ Peak		5x10 <sup>-14</sup>		W/ √ Hz
tr	Response Time	RL = 1 KΩ V <sub>R</sub> = 10 V		50		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.\*\*f=1MHz [FORM NO. 100-PDB-C119-LC REVB]